UNITED STATES PATENT AND TRADEMARK OFFICE **CERTIFICATE OF CORRECTION**

PATENT NO.

: 7,064,358 B2

Page 1 of 1

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INVENTOR(S)

: Indrajlt Manna et al.

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Col. 8, line 15, please replace "p-well" with -- N-well -- before "functioning".

Col. 8, line 53, add --; -- after "a resistor and said p-doped region".

Col. 8, line 58, please replace "grounded-sate" with -- grounded-gate -- before "nMOS".

Col. 9, line 16, please add -- pad -- after "first I/O".

Col. 9, line 22, please replace "p-well" with -- N-well -- after "the deep".

Col. 9, line 50, please replace "fanning" with -- forming -- before "a RC network".

Col. 10, line 24, please replace "p-well" with -- N-well -- before "functioning".

Col. 11, line 4, please replace "p-well" with -- N-well -- before "functioning".

Signed and Sealed this

Second Day of January, 2007

JON W. DUDAS Director of the United States Patent and Trademark Office